2SK3018
Rev.H Sep.-2019

DATA SHEET

/ Descriptions

SOT-23 N MOS N- CHANNEL MOSFET in a SOT-23 Plastic Package.

/ Features

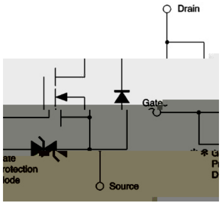
, , , 500V HBM

Low on-resistance, fast switching speed, low voltage drive, easily designed drive circuits, easy to parallel. ESD protected up to 500V HBM .

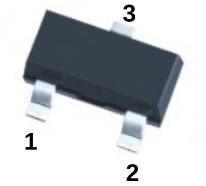
/ Applications

Interfacing, switching.

/ Equivalent Circuit



/ Pinning



PIN1 G PIN 2 S PIN 3 D

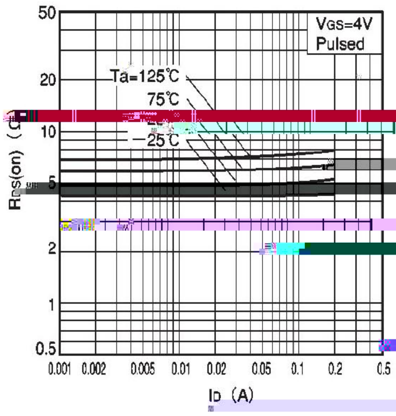
/ Marking

Marking	KL

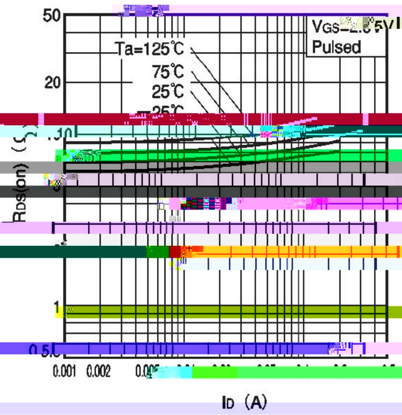
Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	30	V
Gate-Source Voltage	V_{GSS}	±20	V
Drain Current – Continuous	I_D	100	mA
Drain Current- Pulsed	I_{DP}[*1]	400	mA
Reverse Drain Current – Continuous	I_{DR}	100	mA
Reverse Drain Current –Pulsed	I_{DRP}[*1]	200	mA
Total Power Dissipation	P_D[*2]		

/ Electrical Characteristic Curve

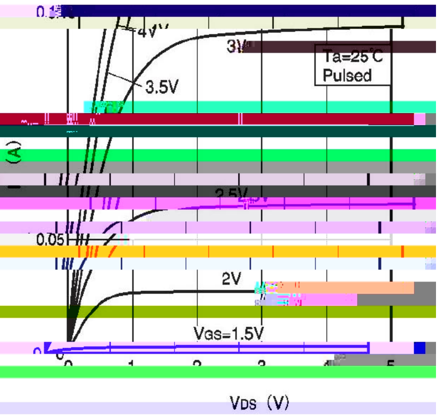
$R_{DS(ON)}$ – I_D



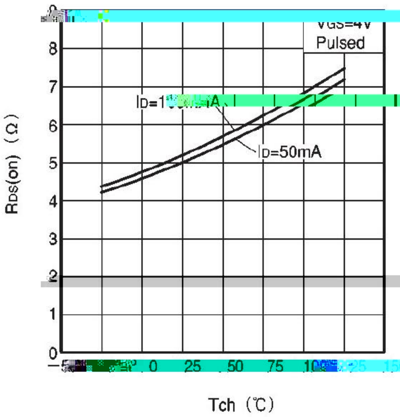
$R_{DS(ON)}$ – I_D



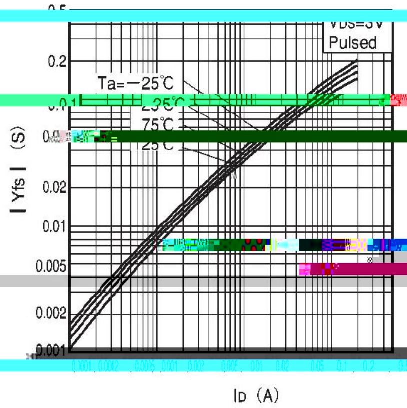
I_D – V_{DS}



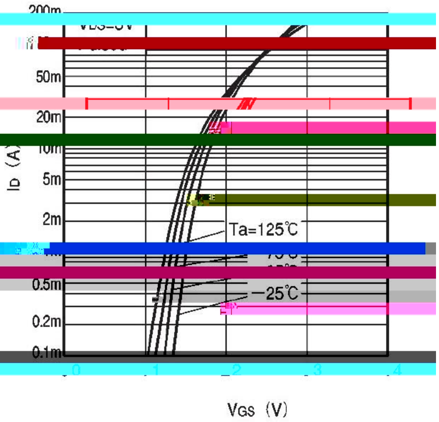
$R_{DS(on)}$ – Tch



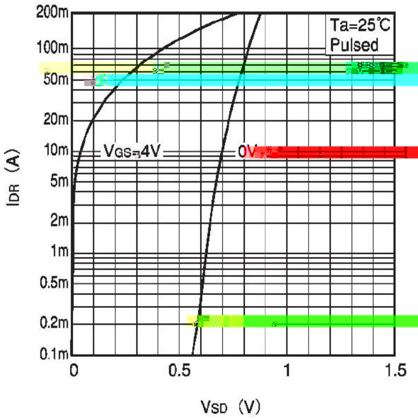
|Yfs| – I_D



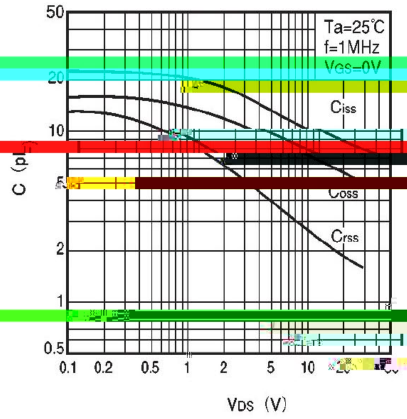
I_D – V_{GS}



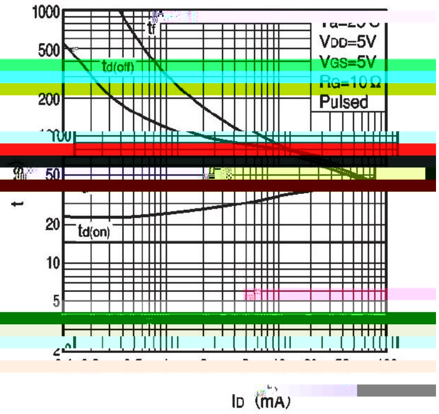
I_{DR} – V_{SD}



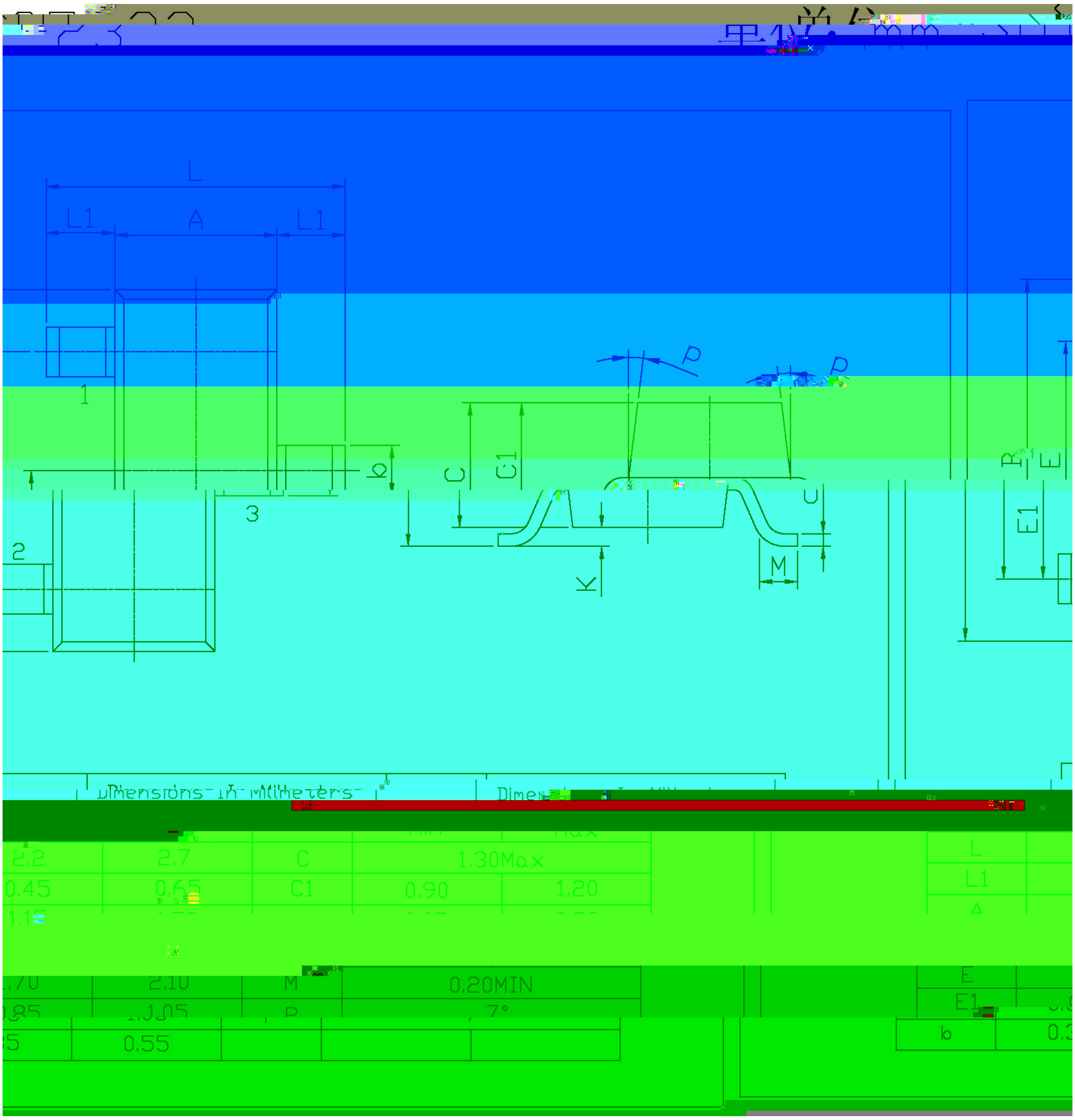
C – V_{DS}



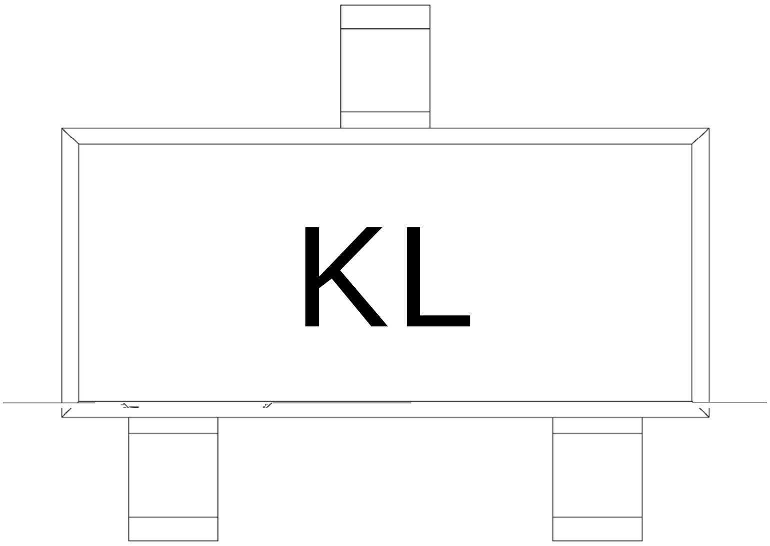
t – I_D



/ Package Dimensions



/ Marking Instructions

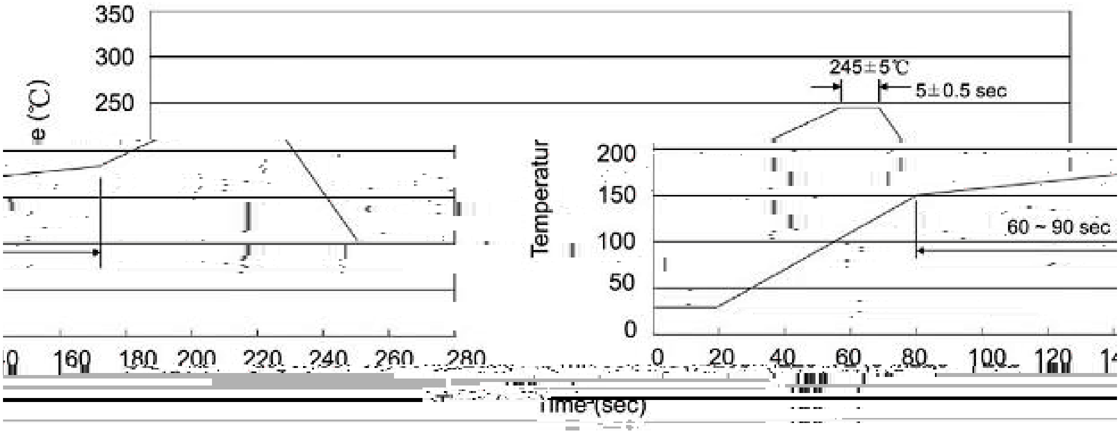


KL:

Note:

KL	Package Type

( ) / Temperature Profile for IR Reflow Soldering(Pb-Free)



Note:

1 150 180 60 90sec;
2 245±5 5±0.5sec;
3 2 10 /sec.

1.Preheating:150~180 , Time:60~90sec.
2.Peak Temp.:245±5 , Duration:5±0.5sec.
3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

260±5 10±1 sec.

Temp.:260±5 Time:10±1 sec

/ Packaging SPEC.

/ REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm^3)		
	只卷盘	卷盘盒	只盒	盒箱	只箱		盒	箱

/ Notices